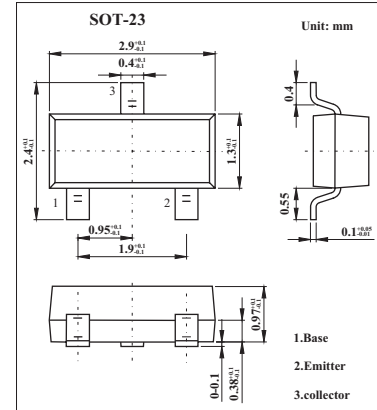


Medium Power Transistor

2SC2411K

■ Features

- High I_{CMax} . $I_{CMax} = 0.5A$
- Low $V_{CE(sat)}$. Optimal for low voltage operation.
- NPN silicon transistor



■ Absolute Maximum Ratings $T_a = 25^\circ C$

| Parameter | Symbol | Rating | Unit |
|-----------------------------|-----------|-------------|------------|
| Collector-base voltage | V_{CBO} | 40 | V |
| Collector-emitter voltage | V_{CEO} | 32 | V |
| Emitter-base voltage | V_{EBO} | 5 | V |
| Collector current * | I_C | 0.5 | A |
| Collector power dissipation | P_C | 0.2 | W |
| Junction temperature | T_j | 150 | $^\circ C$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ C$ |

* P_C must not be exceeded.

■ Electrical Characteristics $T_a = 25^\circ C$

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-----|-----|---------|
| Collector-base breakdown voltage | V_{CBO} | $I_C = 100\mu A$ | 40 | | | V |
| Collector-emitter breakdown voltage | V_{CEO} | $I_C = 1mA$ | 32 | | | V |
| Emitter-base breakdown voltage | V_{EBO} | $I_E = 100\mu A$ | 5 | | | V |
| Collector cutoff current | I_{CBO} | $V_{CB} = 20V$ | | | 1 | μA |
| Emitter cutoff current | I_{EBO} | $V_{EB} = 4V$ | | | 1 | μA |
| DC current gain | h_{FE} | $V_{CE} = 3V, I_C = 100mA$ | 120 | | 390 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C/I_E = 500mA/50mA$ | | | 0.6 | V |
| Output capacitance | C_{ob} | $V_{CB} = 10V, I_E = 0A, f = 1MHz$ | | 6.5 | | pF |
| Transition frequency | f_T | $V_{CE} = 5V, I_E = -20mA, f = 100MHz$ | | 250 | | MHz |

■ h_{FE} Classification

| Marking | CQ | CR |
|----------|---------|---------|
| Rank | Q | R |
| h_{FE} | 120~270 | 180~390 |